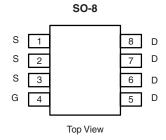




# P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
	0.0075 at V <sub>GS</sub> = - 4.5 V	- 14		
- 20	0.009 at V <sub>GS</sub> = - 2.5 V	- 13		
	0.0115 at V <sub>GS</sub> = - 1.8 V	- 12		



Ordering Information: Si4423DY-T1-E3 (Lead (Pb)-free)

Si4423DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

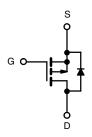
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

# RoHS COMPLIANT HALOGEN

#### **APPLICATIONS**

- · Game Station
  - Load Switch



P-Channel MOSFET

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	- 20		V
Gate-Source Voltage		$V_{GS}$	± 8		V
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 14	- 10	^
	T <sub>A</sub> = 70 °C		- 11.5	- 8	
Pulsed Drain Current		I <sub>DM</sub>	- 50		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 2.7	- 1.36	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.0	1.5	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	T rD	1.9	0.95	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	D	33	42	
Waximum Junction-to-Ambient	Steady State	R <sub>thJA</sub>	70	84	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	16	21	

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.

# Vishay Siliconix



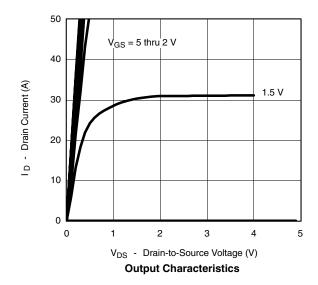
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -600 \mu A$ - 0			- 0.9	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	1	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1		
	IDSS	$V_{DS}$ = - 20 V, $V_{GS}$ = 0 V, $T_{J}$ = 70 °C			- 10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V	- 30			Α	
		$V_{GS} = -4.5 \text{ V}, I_D = -14 \text{ A}$		0.006	0.0075		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -2.5 \text{ V}, I_D = -13 \text{ A}$	do / b		0.009	Ω	
	` ′	$V_{GS} = -1.8 \text{ V}, I_D = -12 \text{ A}$			0.0115		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 14 A		60		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 2.7 A, V <sub>GS</sub> = 0 V		- 0.6	- 1.1	V	
Dynamic <sup>b</sup>			1	•			
Total Gate Charge	Qg			116	175		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -14 \text{ A}$		16		nC	
Gate-Drain Charge	$Q_{gd}$			27		1	
Gate Resistance	$R_g$			3.2		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			75	115		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 10 V, $R_L$ = 10 $\Omega$		165	250	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$		460	700		
Fall Time	t <sub>f</sub>			210	320		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 2.1 A, dl/dt = 100 A/μs		105	160		

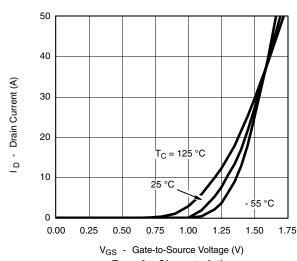
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

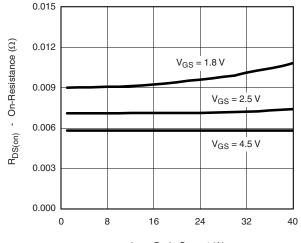


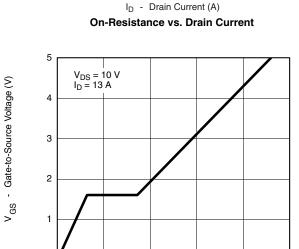






## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





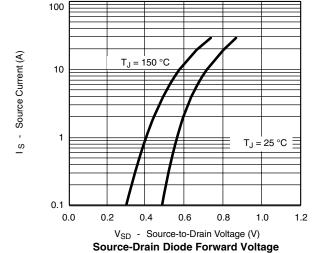
75

Q<sub>g</sub> - Total Gate Charge (nC)

**Gate Charge** 

100

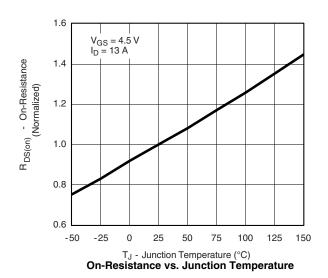
125



12000 10000 10000 8000 0 4000 2000 C<sub>rss</sub> C<sub>rss</sub> 0 0 4 8 12 16 20

V<sub>DS</sub> - Drain-to-Source Voltage (V)

Capacitance



0.030
0.024
0.018
0.012
0.012
0.000
0.000
0.000
1.6 3.2 4.8 6.4 8.0
V<sub>GS</sub> - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage

0

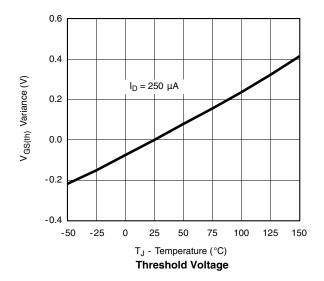
0

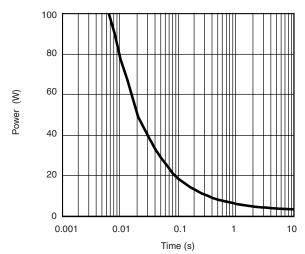
25

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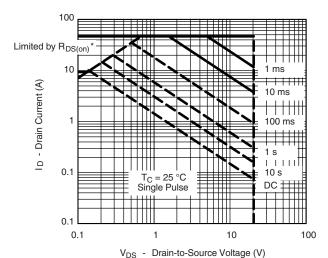
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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



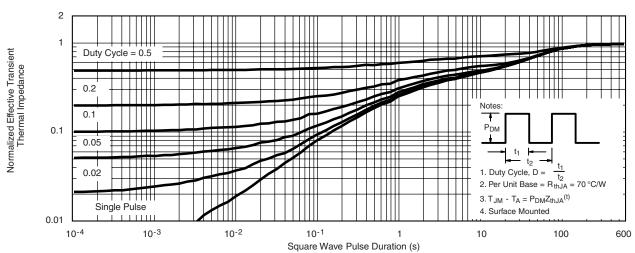


Single Pulse Power, Junction-to-Ambient



\*  $\rm V_{GS} > minimum \ V_{GS}$  at which  $\rm R_{DS(on)}$  is specified

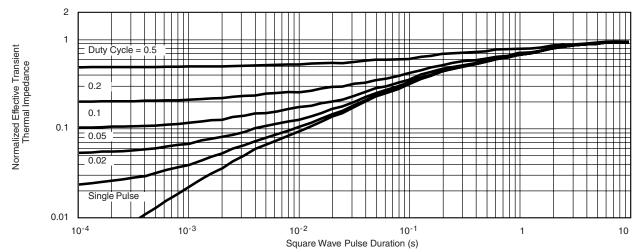
#### Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?72085">www.vishay.com/ppg?72085</a>.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



## **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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